IN THE CLAIMS

Please cancel claims 12 through 16 without prejudice or disclaimer, and maintain claims 1-11 and 17-19, as follows:

1. (previously presented) A method for manufacturing a semiconductor device wherein for a substrate as a workpiece in which an insulation film is formed to the substrate, openings are formed in the insulation film, a first conductive film is formed in an inside of the openings and on a surface of the insulation film, a second conductive film is formed on the first conductive film, and the first and the second conductive film are formed in the openings by planarizing a surface of the second conductive film and a surface of part of the first conductive film using a fixed abrasive tool, said method comprising the steps of:

supplying a first processing liquid including about 30% oxidizing agent;

planarizing the surface of the second conductive film with the first processing liquid and said fixed abrasive tool;

switching the supply of the liquid from first processing liquid to a second processing liquid including about 5% oxidizing agent; and

planarizing the surface of the second conductive film and the surface of the part of the first conductive film with the second processing liquid and said fixed abrasive tool,

wherein a plurality of planarizing steps are constituted in a single planarizing step.

2. (previously presented) A method for manufacturing a semiconductor device according to claim 1, further comprising:

dressing a surface of the fixed abrasive tool before said planarization of the surface of the second conductive film and the surface of the part of the first conductive film.

3. (previously presented) A method for manufacturing a semiconductor device wherein for a substrate as a workpiece in which an insulation film is formed to the substrate, openings are formed in the insulation film, a first conductive film is formed in inside of the openings and on a surface of the insulation film, a second conductive film is formed on the first conductive film, and the first and the second conductive film are

formed in the openings by planarizing a surface of the second conductive film and a surface of part of the first conductive film using a fixed abrasive tool, said method comprising the steps of:

supplying a first processing liquid including about 30% oxidizing agent;

planarizing the surface of the second conductive film with the first processing liquid and said fixed abrasive tool;

switching the supply of the liquid from first processing liquid to a second processing liquid including about 5% oxidizing agent;

dressing a surface of the fixed abrasive tool before planarization of the surface of the second conductive film and the surface of the part of the first conductive film; and

planalizing the surface of the second conductive film and the surface of the part of the first conductive film with the second processing liquid and said fixed abrasive tool,

wherein a plurality of planarizing steps are constituted in a single planarizing step.

4. (previously presented) A method for manufacturing a semiconductor device as defined in claim 1, wherein a distance of the insulative film between adjacent openings is within a range of 30 μm to 0.1 μm, and dishing and erosion on the planarized surface is 40 nm or less.

5. (previously presented) A method for manufacturing a semiconductor device as defined in claim 1, wherein each of the first and the second processing liquid contains an oxidizing agent, an organic acid, a corrosion inhibitor and purified water.

6. (original) A method for manufacturing a semiconductor device as defined in claim 5, wherein each of the first and the second processing liquid contains aqueous hydrogen peroxide, malic acid, benzotriazole and purified water.

7. (original) A method for manufacturing a semiconductor device as defined in claim 6, wherein each of the first and the second processing liquid contains from 0.5 to 50% of aqueous hydrogen peroxide, from 0.1 to 0.2% of malic acid and from 0.1 to 0.4% of benzotriazole.

8. (original) A method for manufacturing a semiconductor device as defined in claim 5, wherein the abrasive grains of the fixed abrasive tool comprise fumed silica and the abrasive grains are fixed with a resin.

9. (previously presented) A method for manufacturing a semiconductor device according to claim 1, wherein said polishing step proceeded with the use of the abrasive tool, said abrasive tool comprising a plurality of abrasive grains including fumed silica and a resin to fix the abrasive grain.

10. (original) A method for manufacturing a semiconductor device as defined in claim 9, wherein the fumed silica abrasive grains are fixed with a resin and a compression modulus of elasticity is from 500 Mpa to 1000 Mpa.

11. (original) A method for manufacturing a semiconductor device as defined in claim 2, wherein the dressing is conducted by using a diamond dresser and the height of the diamond dresser from the surface of the fixed abrasive tool can be positioned.

12-16. (canceled)

17. (original) A method for manufacturing a semiconductor device as defined in claim 2, wherein the distance of the insulative film between adjacent openings is within a range of 30 μm to 0.1 μm, and dishing and erosion on the planarized surface is 40 nm or less.

18. (original) A method for manufacturing a semiconductor device as defined in claim 3, wherein each of the first and the second processing liquid contains an oxidized agent, an organic acid, a corrosion inhibitor and purified water.

19. (original) A method for manufacturing a semiconductor device as defined in claim 2, wherein the abrasive grains of the fixed abrasive tools comprise fumed silica and the abrasive grains are fixed with a resin.